



700V Super-Junction Power MOSFET

DESCRIPTION

700V super-junction Power MOSFET

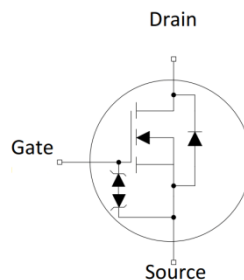
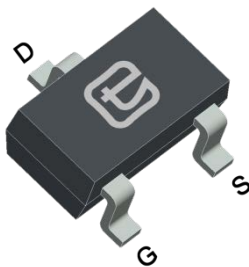
Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs, designed according to the SJ principle. The SJ MOSFET is a price-performance optimized product enabling to target cost sensitive applications in Consumer and Lighting markets, designed by Wuxi Unigroup Microelectronics Company.

FEATURES

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant
- Integrated ESD protection diode

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information

Device	Package	Marking
TPY70R1K5MB	SOT-223-2L	70R1K5M

Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	700	V
$R_{DS(on),max}$	1.5	Ω
I_D	3	A
$Q_{g,typ}$	7	nC
I_{DM}	9	A
ESD class (HBM)	1C	



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	700	V
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$	3
		$T_C = 100^\circ\text{C}$	1.8
Pulsed Drain Current (note1)	I_{DM}	9	A
Gate-Source Voltage	V_{GSS}	± 20	V
Single Pulse Avalanche Energy (note2)	E_{AS}	26	mJ
Repetitive Avalanche Energy (note2)	E_{AR}	0.10	mJ
Avalanche Current	I_{AR}	0.6	A
MOSFET dv/dt ruggedness, $V_{DS} = 0 \dots 480\text{V}$	dv/dt	50	V/ns
Power Dissipation	P_D	6.2	W
Continuous Body Diode Current	I_S	2.5	A
Pulsed Diode Forward Current (note1)	I_{SM}	33	
Reverse diode dv/dt (note3)	dv/dt	15	V/ns
Maximum diode commutation speed (note3)	di/dt	500	A/us
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	20	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	160	



Specifications $T_J = 25^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	700	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 700V, V_{GS} = 0V, T_J = 25^{\circ}\text{C}$	--	--	1	μA
		$V_{DS} = 700V, V_{GS} = 0V, T_J = 150^{\circ}\text{C}$	--	--	100	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V$	--	--	± 1	μA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	--	4.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1.5A$	--	1.3	1.5	Ω
Gate resistance	R_G	$f = 1.0\text{MHz}$ open drain	--	5.5	--	Ω
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 100V,$ $f = 1.0\text{MHz}$	--	225	--	μF
Output Capacitance	C_{oss}		--	10	--	
Reverse Transfer Capacitance	C_{rss}		--	0.4	--	
Total Gate Charge	Q_g	$V_{DD} = 560V, I_D = 3A,$ $V_{GS} = 10V$	--	7	--	nC
Gate-Source Charge	Q_{gs}		--	1.3	--	
Gate-Drain Charge	Q_{gd}		--	3.5	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 3A,$ $R_G = 25\Omega$	--	8.5	--	ns
Turn-on Rise Time	t_r		--	7.7	--	
Turn-off Delay Time	$t_{d(off)}$		--	19.0	--	
Turn-off Fall Time	t_f		--	16.5	--	
Drain-Source Body Diode Characteristics						
Body Diode Voltage	V_{SD}	$T_J = 25^{\circ}\text{C}, I_{SD} = 1.5A, V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R = 400V, I_F = 3A,$ $di_F/dt = 100A/\mu s$	--	155	--	ns
Reverse Recovery Charge	Q_{rr}		--	0.85	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	11	--	A

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 0.6A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$
3. Identical low side and high side switch with identical R_G



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

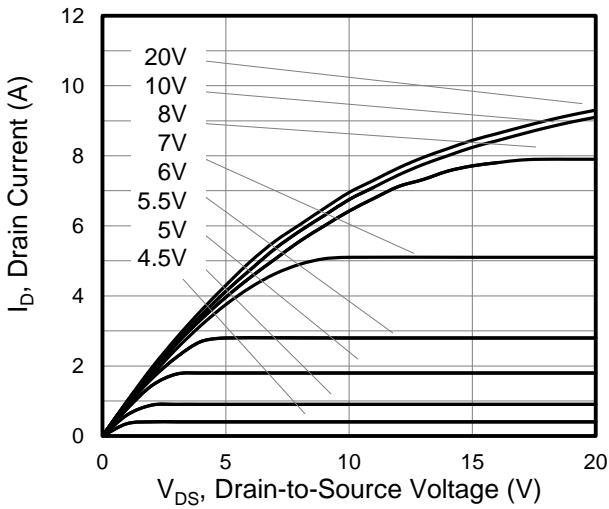


Figure 2. Transfer Characteristics

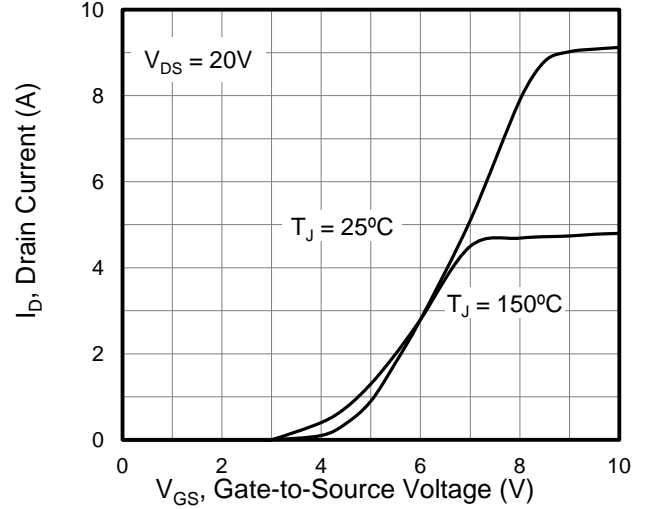


Figure 3. On-Resistance vs. Drain Current

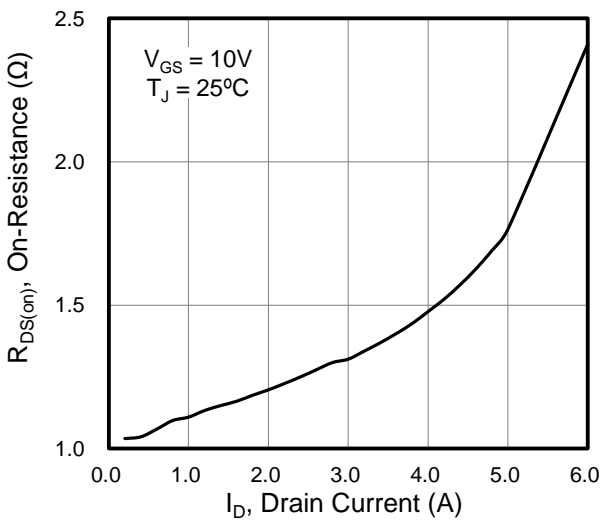


Figure 4. Capacitance

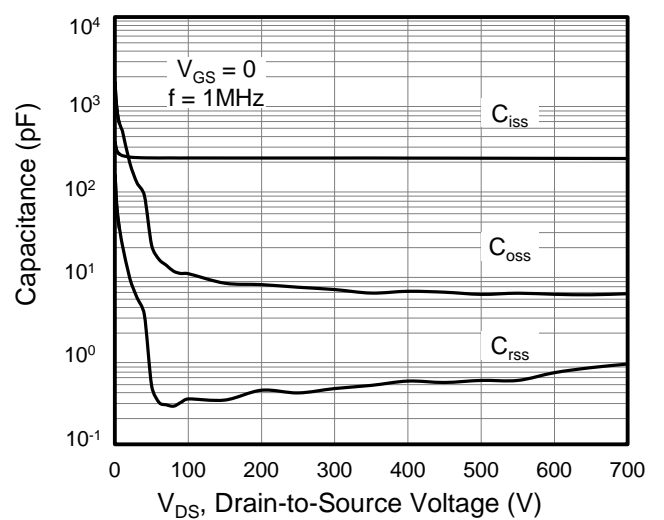


Figure 5. Gate Charge

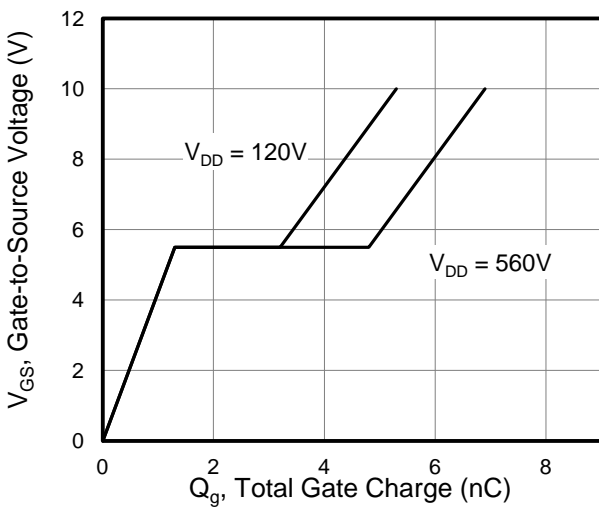
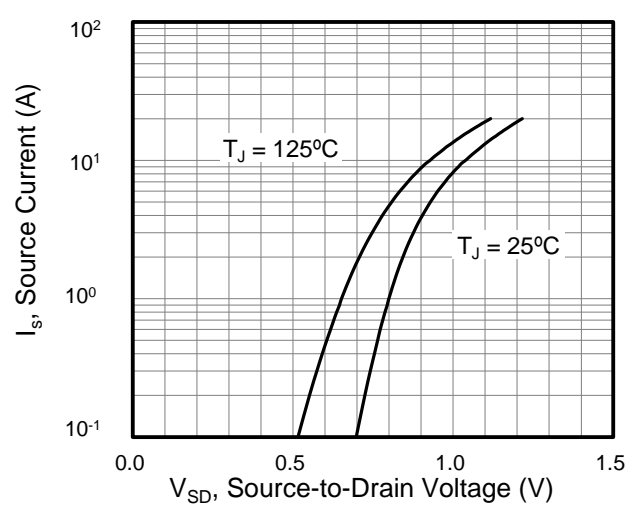


Figure 6. Body Diode Forward Voltage





Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

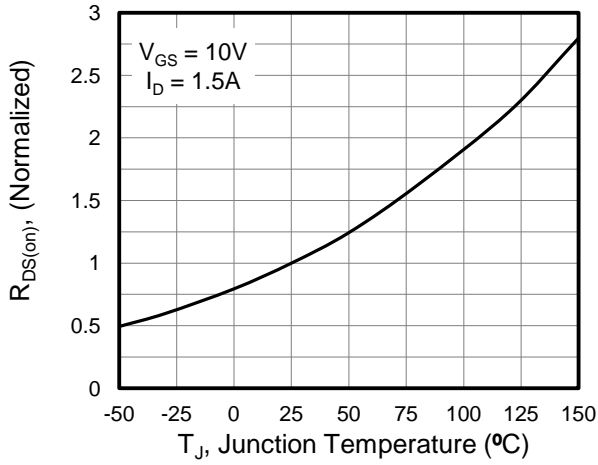


Figure 8. Breakdown voltage vs. Junction Temperature

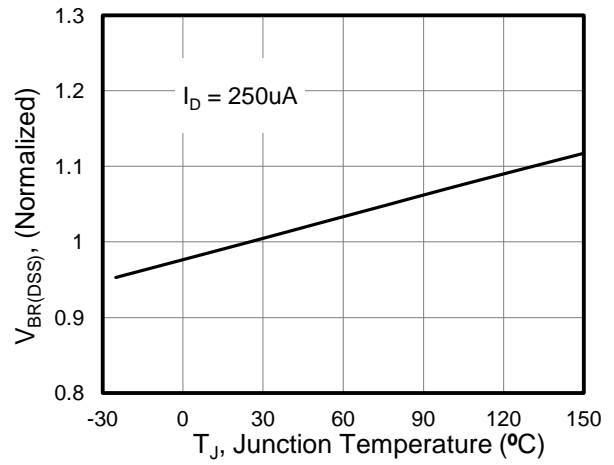


Figure 9. Transient Thermal Impedance for SOT-223-2L

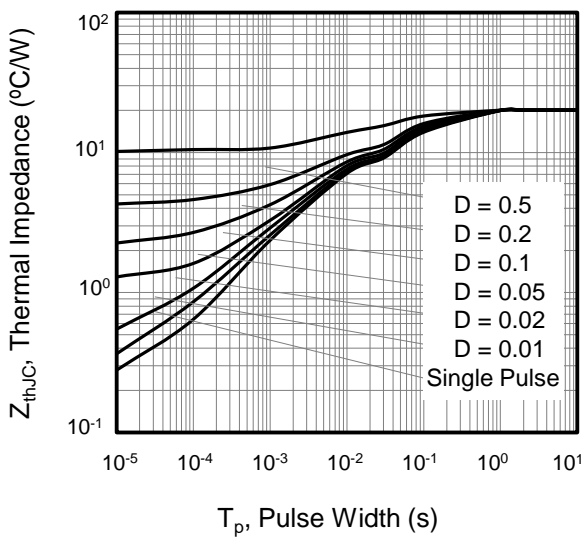


Figure 10. Safe operation area for SOT-223-2L

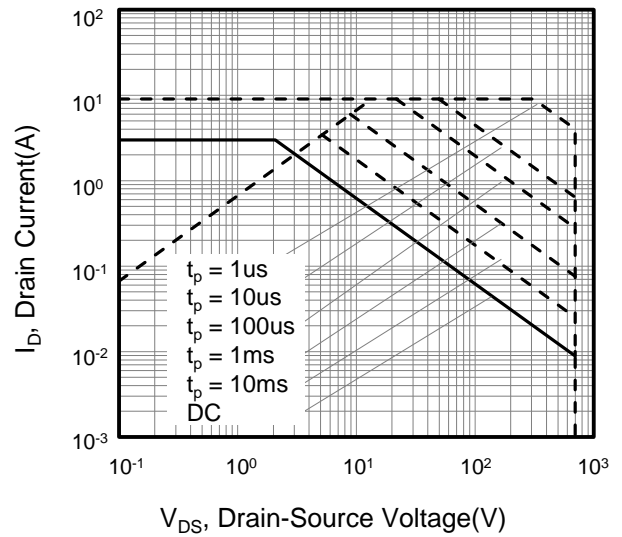




Figure A: Gate Charge Test Circuit and Waveform

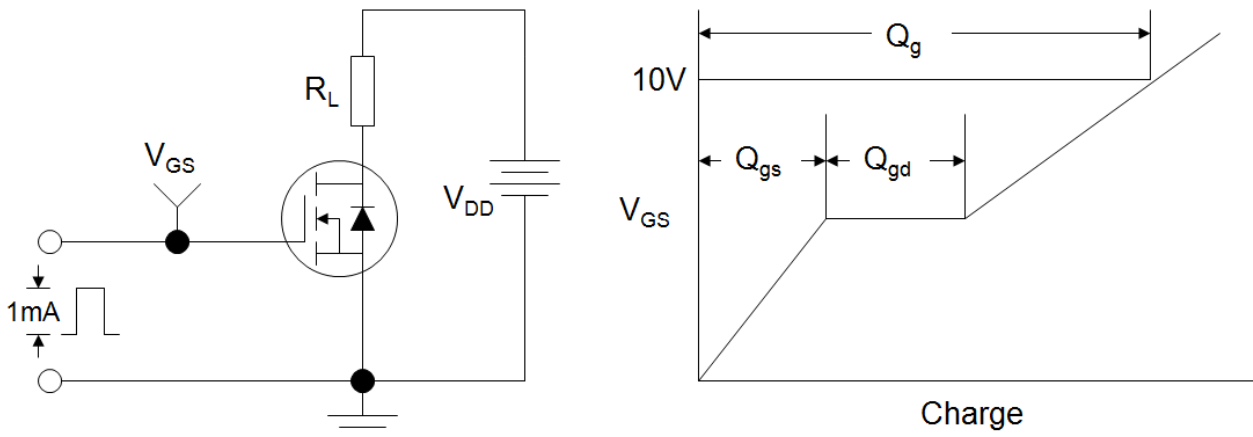


Figure B: Resistive Switching Test Circuit and Waveform

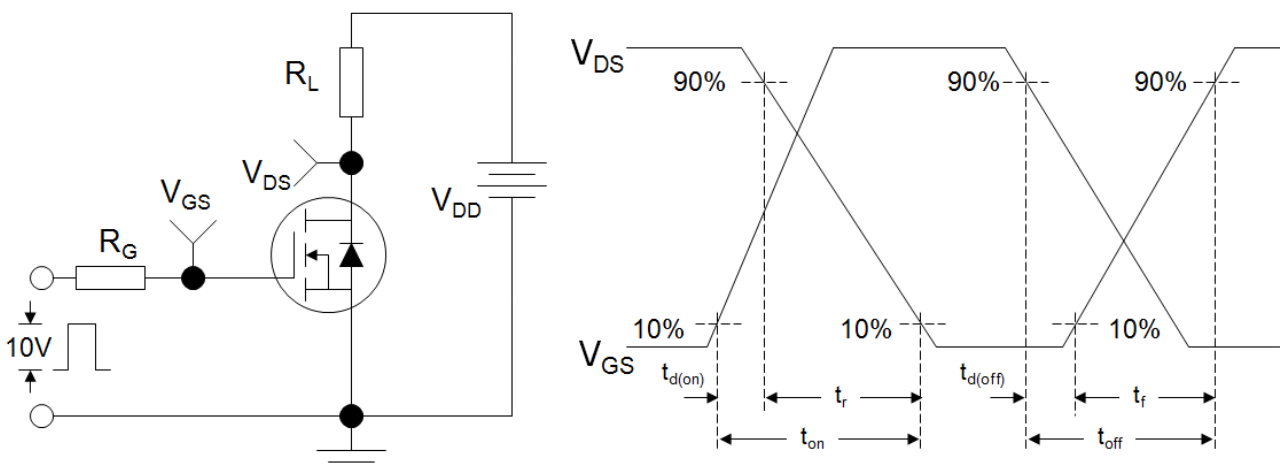
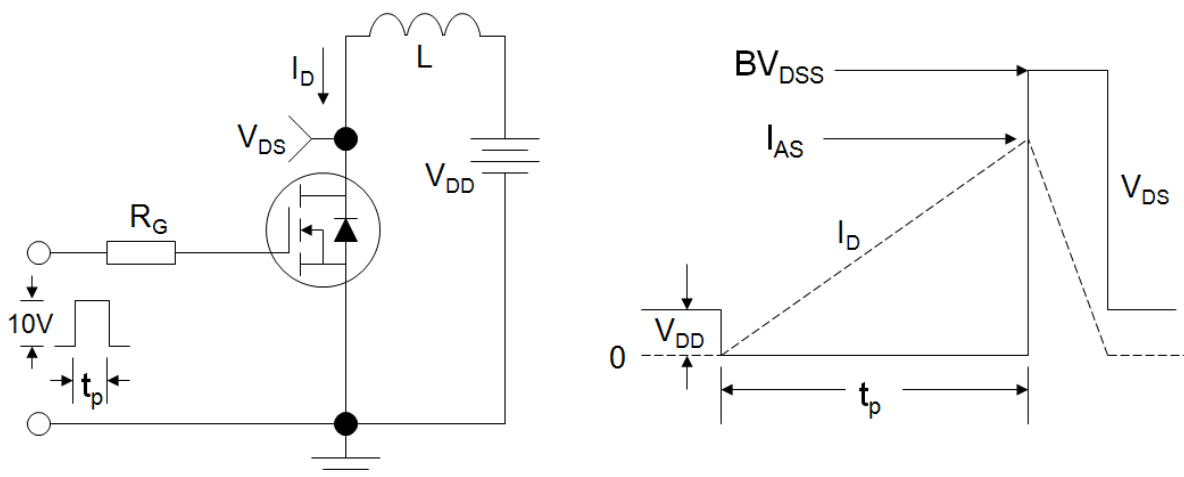
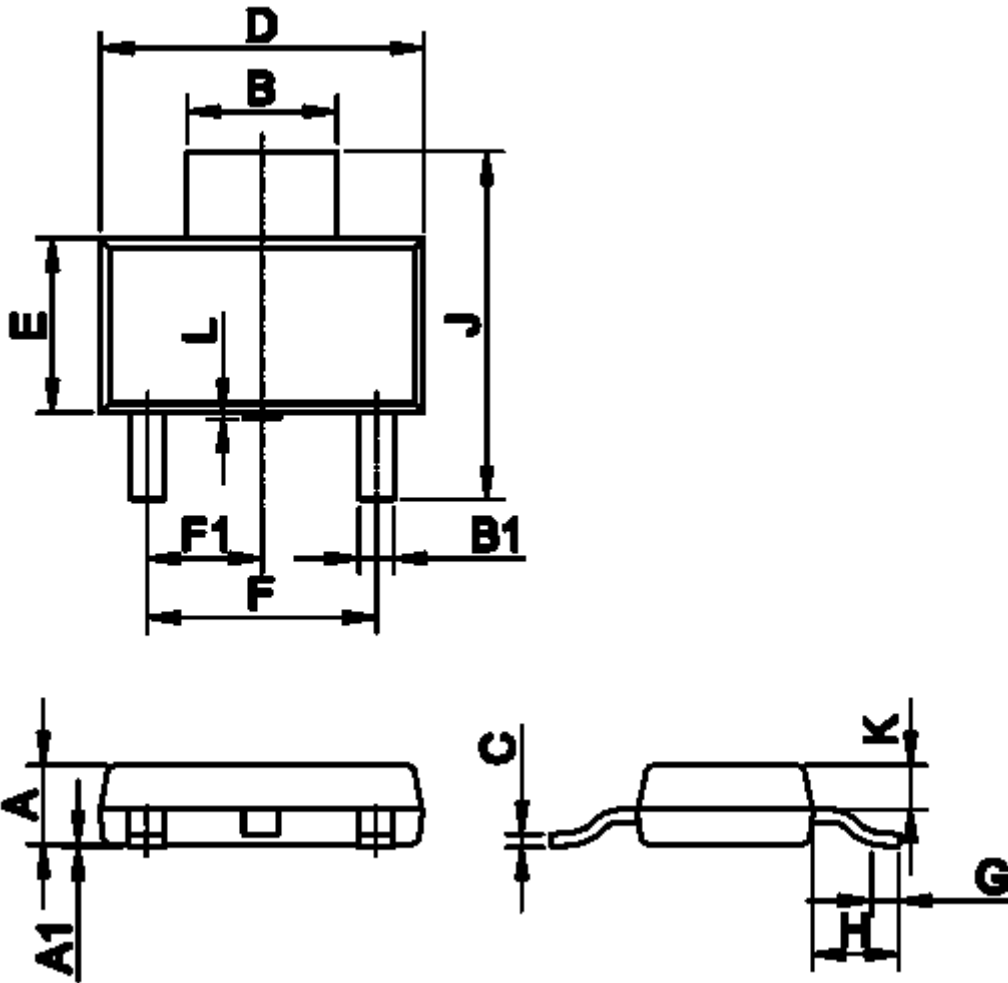


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





SOT-223-2L



Unit:mm			
Symbol	Min.	Typ.	Max.
A	1.50	1.60	1.80
A1	0.01	0.06	0.10
B	2.90	3.00	3.10
B1	0.60	0.07	0.80
C	0.22	0.254	0.32
D	6.30	6.50	6.70
E	3.30	3.50	3.70

Unit:mm			
Symbol	Min.	Typ.	Max.
F		4.60	
F1		2.30	
G	0.70	0.90	1.10
H	1.50	1.75	2.00
J	6.70	7.00	7.30
K		0.90	
L	0	0.10	0.20



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